Darlington Transistor

multicomp



Features:

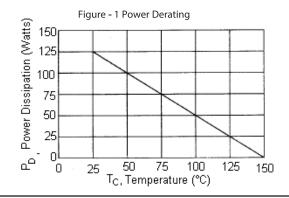
- Collector-Emitter sustaining voltage - VCEO(sus) = 80V (Min.) - BDV66A, BDV67A
 - = 100V (Min.) BDV66B, BDV67B
- Collector-Emitter saturation voltage
 - VCE(sat) = 2V (Max.) at Ic = 10A
- · Monolithic construction with Built-in Base-Emitter Shunt Resistor

Maximum Ratings

Characteristic	Symbol	BDV66A BDV67A	BDV66B BDV67B	Unit
Collector-Emitter Voltage	Vceo	80	100	V
Collector-Base Voltage	Vсво	80		
Emitter-Base Voltage	Vebo	5		1
Collector Current - Continuous - Peak	Іс Ісм	16 20		A
Base Current	Ів	0.25		1
Total Power Dissipation at Tc = 25°C Derate above 25°C	Po	125 1		W W/°C
Operation and Storage Junction Temperature Range	TJ, TSTG	-65 to +150		°C

Thermal Characteristics

Characteristic	Symbol	Max.	Unit
Thermal Resistance Junction to Case	Rθjc	1	°C/W



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BDV67B

TO-247(3P)

BDV66B

16 Ampere Darlington Complementary Silicon Power Transistors 60 - 100 Volts 125 Watts

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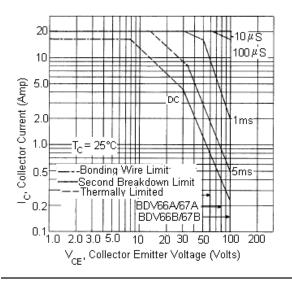
Electrical Characteristics (Tc = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit	
OFF Characteristics				•	
Collector-Emitter Sustaining Voltage (1) (Ic = 0.1A, L = 25mH) BDV66A, BDV67A BDV66B, BDV67B	VCEO(sus)	80 100	-	V	
Collector Cut off Current BDV66A, BDV67A (VCE = 40V, IB = 0) BDV66B, BDV67B	ICEO	-	3	mA	
Collector Cut off Current (V _{CB} = 80V, I _E = 0) BDV66A, BDV67A (V _{CB} = 100V, I _E = 0) BDV66B, BDV67B	Ісво	-	0.4		
Emitter Cut off Current (V _{EB} = 5V, Ic = 0)	Іево	-	5		
ON Characteristics (1)					
Collector-Emitter Saturation Voltage (Ic = 10A, IB = 40mA)	VCE(sat)	-	2	V	
Dynamic Characteristics					
Small-Signal Current Gain (2)(Ic = 5A, VCE = 3V, f = 1KHz)	fτ	6	-	MHz	
Output Capacitance (V _{CB} = 10V, I _E = 0, f = 1MHz)	Cob	-	450	pF	
Switching Characteristics					
Turn On TimeIc = 5A, Vcc = 12V	ton	1 (typical)	-		
Off Time IB1 = -IB2 = 40mA	toff	3.5 (typical)	-	μs	

(1) Pulse Test: Pulse Width = 300µs, Duty Cycle ≤2%

(2) $f_T = |h_{FE}| \cdot f_{test}$

Figure - 2 Active-Region Safe Operating Area

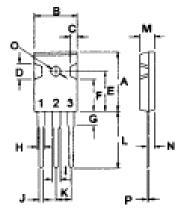


There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate Ic-VCE limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure-2 is based on T_J(PK) = 150°C; Tc is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided T_J(PK) <150°C. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

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Dimensions	Minimum	Maximum
A	20.63	22.38
В	15.38	16.2
С	1.9	2.7
D	5.1	6.1
E	14.81	15.22
F	11.72	12.84
G	4.2	4.5
Н	1.82	2.46
I	2.92	3.23
J	0.89	1.53
K	5.26	5.66
L	18.5	21.5
М	4.68	5.36
N	2.4	2.8
0	3.25	3.65
Р	0.55	0.7

Dimensions : Millimetres

Part Number Table

Description	Туре	Part Number
	NPN	BDV67A
Darlington Transistor	INFIN	BDV67B
	PNP	BDV66A
		BDV66B

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